EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10426	257/369.ccls. 257/388.ccls. 257/407.ccls. 257/410.ccls. 257/411.ccls. 257/412.ccls. 257/ e21.199.ccls. 257/ e29.161.ccls. 438/216. ccls. 438/287.ccls. 438/591.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR		2009/01/23 08:01
L2	432	L1 and ((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid \$8 disilicide))) same (gate electrode control) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/01/23 08:01
L3	271	L1 and ((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid \$8 disilicide))) same (gate electrode control) same (insulat \$6 dielectric oxide dioxide) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR		2009/01/23 08:04

L4	17	L1 and ((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid \$8 disilicide))) same ((gate electrode control) with (insulat \$6 dielectric oxide dioxide) with (high near2 (k permittivity (dielectric adj constant)))) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/01/23 08:12
L5	56	L1 and (((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid \$8 disilicide))) with (full\$3 entir\$6 completely anneal\$6 heat\$6 treat\$6 rta rtp thermal\$6)) same (gate electrode control) same (insulat \$6 dielectric oxide dioxide) same (cmos complementary pmos nmos channel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/01/23 08:16
L6	49		US-PGPUB; USPAT	OR	ON	2009/01/23

L7	17	((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) with (full \$3 entir\$6 completely (direct\$6 near2 contact\$6)) with (anneal\$6 heat\$6 treat\$6 rta rtp thermal \$6)) same (gate electrode control) same (insulat\$6 dielectric oxide dioxide) same (cmos complementary pmos nmos channel)	US-PGPUB; USPAT	OR	ON	2009/01/23
L8	15	((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) with (gate electrode control)) and ((insulat\$6 dielectric oxide dioxide) with (high near2 (k permittivity (dielectric adj constant)))) and (cmos complementary pmos nmos channel)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR		2009/01/23
L9	137	((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) same (full \$3 entir\$6 completely anneal\$6 heat\$6 treat \$6 rta rtp thermal\$6)) and (gate electrode control) and (insulat \$6 dielectric oxide dioxide) and (cmos complementary pmos nmos channel)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/23

L10	13	((ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) same (full \$3 entir\$6 completely (direct\$6 near2 contact\$6)) same (anneal\$6 heat\$6 treat\$6 rta rtp thermal \$6)) and (gate electrode control) and (insulat\$6 dielectric oxide dioxide) and (cmos complementary pmos nmos channel)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/23 09:14
L11	37	(ptsi cosi zrsi tasi tisi vsi hfsi ((platinum cobalt zirconium tantalum titanium vanadium hafnium) near2 (silicid\$8 disilicide))) and (full \$3 entir\$6 completely (direct\$6 near2 contact\$6)) and (anneal\$6 heat\$6 treat\$6 rta rtp thermal \$6) and (gate electrode control) and (insulat\$6 dielectric oxide dioxide) and (cmos complementary pmos nmos channel)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/23 09:15

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